TOSHIBA Photocoupler Photorelay

TLP4192G

Telecommunication Measurement Equipment Security Equipment FA

The Toshiba TLP4192G consists of an aluminum gallium arsenide infrared emitting diode optically coupled to a photo-MOSFET in a SOP package. This 1-form-B (NC) photorelay features a withstanding voltage of $350~\rm V$.

• 6-pin SOP (2.54SOP6): Height = 2.1 mm, pitch = 2.54 mm

• Normally closed (1-form-B) device

• Peak off-state voltage: 350 V (min)

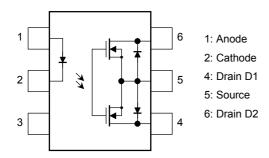
• Trigger LED current: 3 mA (max)

• On-state current: 90 mA (max)

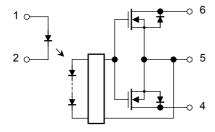
• On-state resistance: 50Ω (max)

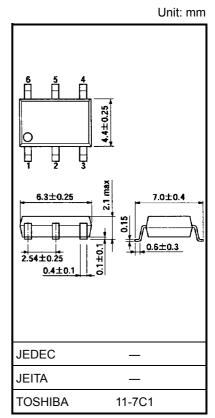
• Isolation voltage: 1500 Vrms (min)

Pin Configuration (top view)



Schematic





Weight: 0.13 g (typ.)

Maximum Ratings (Ta = 25°C)

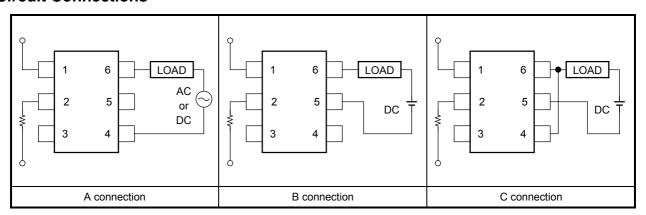
	Characteristics	Symbol	Rating	Unit		
	Forward current	lF	50	mA		
	Forward current derating (Ta	ΔI _F /°C	-0.5	mA/°C		
LED	Peak forward current (100 μs	pulse, 100 pps)	I _{FP}	1	Α	
	Reverse voltage		V _R	5	V	
	Junction temperature		Tj	125	°C	
	Off-state output terminal volta	V _{OFF}	350	V		
	On-state current	A connection		90		
		B connection	I _{ON}	90	mA	
Detector		C connection		180		
Dete	On-state current derating (Ta ≧ 25°C)	A connection		-0.9		
		B connection	Δl _{ON} /°C	-0.9	mA/°C	
		C connection		-1.8		
	Junction temperature	•	Tj	125	°C	
Storage temperature range			T _{stg}	-55 to 125	°C	
Operating temperature range			T _{opr}	-40 to 85	°C	
Lead soldering temperature (10 s)			T _{sol}	260	°C	
Isola	tion voltage (AC, 1 min, R.H. ≦	BVS	1500	Vrms		

Note 1: Pins 1, 2 and 3 are shorted together, and pins 4, 5 and 6 are shorted together.

Recommended Operating Conditions

Characteristics	Symbol	Min	Тур.	Max	Unit
Supply voltage	V_{DD}	_	_	280	V
Forward current	lF	5	_	25	mA
On-state current	I _{ON}	_	_	90	mA
Operating temperature	T _{opr}	-20		65	°C

Circuit Connections



Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
	Forward voltage	V _F	I _F = 10 mA	1.0	1.15	1.3	V
LED	Reverse current	I _R	V _R = 5 V	_	_	10	μА
	Capacitance	C _T	V = 0, f = 1 MHz	_	30	_	pF
ctor	Off-state current	l _{OFF}	V _{OFF} = 350 V, I _F = 5 mA	_	_	1	μА
Detector	Capacitance	C _{OFF}	V = 0, f = 1 MHz, I _F = 5 mA	_	30	_	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Trigger LED current		I _{FC}	I _{OFF} = 10 μA	_	1	3	mA
Return LED current		I _{FT}	I _{ON} = 90 mA	0.1	_	_	mA
	A connection		I _{ON} = 90 mA	_	27	50	
On-state resistance	B connection	R _{ON}	I _{ON} = 90 mA	_	20	43	Ω
	C connection		I _{ON} = 180 mA	_	10	_	

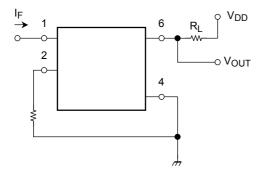
Isolation Characteristics (Ta = 25°C)

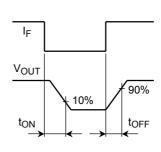
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Capacitance input to output	CS	V _S = 0, f = 1 MHz	_	0.8	_	pF
Isolation resistance	R _S	V _S = 500 V, R.H. ≦ 60%	5×10^{10}	10 ¹⁴	_	Ω
		AC, 1 min	1500	_	_	Vrms
Isolation voltage		AC, 1 s, in oil	_	3000	_	VIIIIS
		DC, 1 min, in oil	_	3000		Vdc

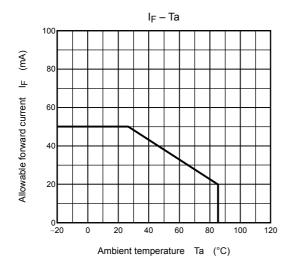
Switching Characteristics (Ta = 25°C)

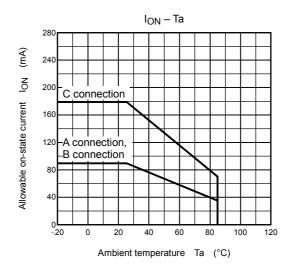
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Turn-on time	t _{ON}	$R_L = 200 \Omega$	_	0.25	0.5	ms
Turn-off time	toff	$V_{DD}^{-} = 20 \text{ V, I}_{F} = 5 \text{ mA}$ (Note 2)	_	0.5	1	ms

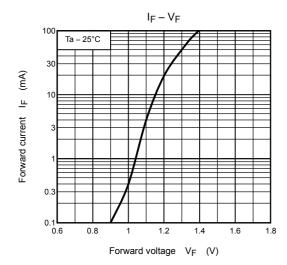
Note 2: Switching time test circuit



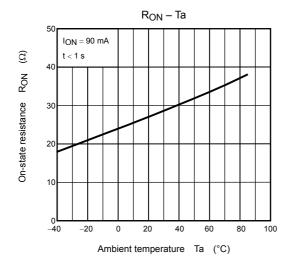


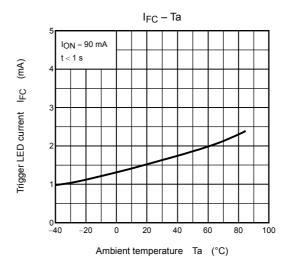


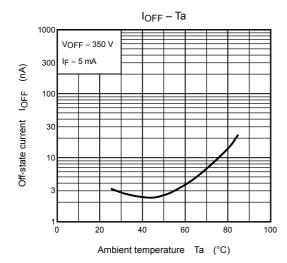


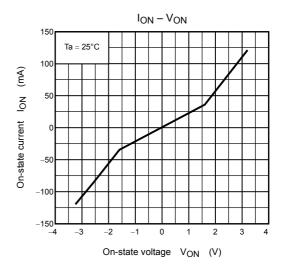


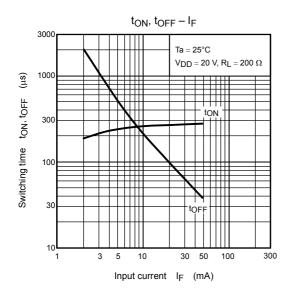
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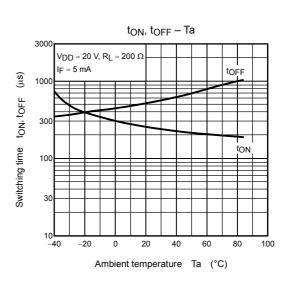












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